

HiPerDynFRED

$$V_{RRM} = 1800\text{ V}$$

$$I_{FAV} = 2 \times 25\text{ A}$$

$$t_{rr} = 30\text{ ns}$$

High Performance Dynamic Fast Recovery Diode
 Extreme Low Loss and Soft Recovery
 Parallel legs with series connected dice

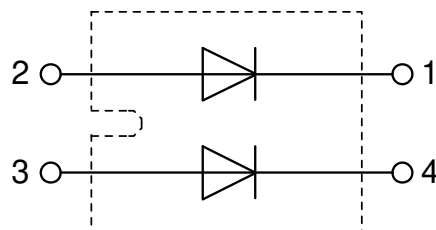
Part number

DPJ50XS1800NA



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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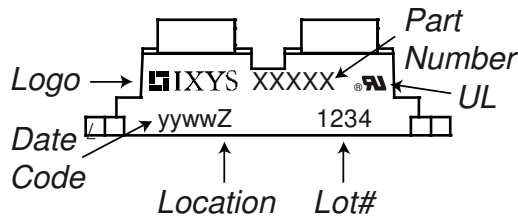


| Fast Diode | | | | Ratings | | | |
|------------|--|---|-------------------------|---------|------|------------|--|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit | |
| V_{RSM} | max. non-repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1800 | V | |
| V_{RRM} | max. repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1800 | V | |
| I_R | reverse current, drain current | $V_R = 1800 V$ | $T_{VJ} = 25^{\circ}C$ | | 250 | μA | |
| | | $V_R = 1800 V$ | $T_{VJ} = 150^{\circ}C$ | | 2 | mA | |
| V_F | forward voltage drop | $I_F = 25 A$ | $T_{VJ} = 25^{\circ}C$ | | 6.99 | V | |
| | | $I_F = 50 A$ | | | 8.72 | V | |
| | | $I_F = 25 A$ | $T_{VJ} = 150^{\circ}C$ | | 4.33 | V | |
| | | $I_F = 50 A$ | | | 5.83 | V | |
| I_{FAV} | average forward current | $T_C = 90^{\circ}C$ rectangular $d = 0.5$ | $T_{VJ} = 150^{\circ}C$ | | 25 | A | |
| V_{FO} | threshold voltage | } for power loss calculation only | $T_{VJ} = 150^{\circ}C$ | | 2.92 | V | |
| r_F | slope resistance | | | | 56 | m Ω | |
| R_{thJC} | thermal resistance junction to case | | | | 0.4 | K/W | |
| R_{thCH} | thermal resistance case to heatsink | | | 0.1 | | K/W | |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}C$ | | 315 | W | |
| I_{FSM} | max. forward surge current | $t = 10 ms; (50 Hz), sine; V_R = 0 V$ | $T_{VJ} = 45^{\circ}C$ | | 250 | A | |
| C_J | junction capacitance | $V_R = 900 V \quad f = 1 MHz$ | $T_{VJ} = 25^{\circ}C$ | | 10 | pF | |
| I_{RM} | max. reverse recovery current | } $I_F = 30 A; V_R = 900 V$ $-di_F / dt = 400 A/\mu s$ | $T_{VJ} = 25^{\circ}C$ | | 9 | A | |
| | | | $T_{VJ} = 125^{\circ}C$ | | 13 | A | |
| t_{rr} | reverse recovery time | | $T_{VJ} = 25^{\circ}C$ | | 30 | ns | |
| | | | $T_{VJ} = 125^{\circ}C$ | | 140 | ns | |



| Package SOT-227B (minibloc) | | | | Ratings | | | |
|-----------------------------|--|----------------------|-------------------------------------|---------|------|------|--|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit | |
| I_{RMS} | RMS current | per terminal | | | 100 | A | |
| T_{VJ} | virtual junction temperature | | -40 | | 150 | °C | |
| T_{op} | operation temperature | | -40 | | 125 | °C | |
| T_{stg} | storage temperature | | -40 | | 150 | °C | |
| Weight | | | | | 30 | g | |
| M_D | mounting torque | | 1.1 | | 1.5 | Nm | |
| M_T | terminal torque | | 1.1 | | 1.5 | Nm | |
| $d_{Spp/App}$ | creepage distance on surface striking distance through air | terminal to terminal | 10.5 | 3.2 | | mm | |
| $d_{Spb/Apb}$ | | terminal to backside | 8.6 | 6.8 | | mm | |
| V_{ISOL} | isolation voltage | t = 1 second | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 3000 | | V | |
| | | t = 1 minute | | 2500 | | V | |

Product Marking



Part description

- D = Diode
- P = HiPerFRED
- J = HiPerDyn +
- 50 = Current Rating [A]
- XS = Parallel legs with series connected dice
- 1800 = Reverse Voltage [V]
- NA = SOT-227B (minibloc)

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | DPJ50XS1800NA | DPJ50XS1800NA | Tube | 10 | 517619 |

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Fast Diode

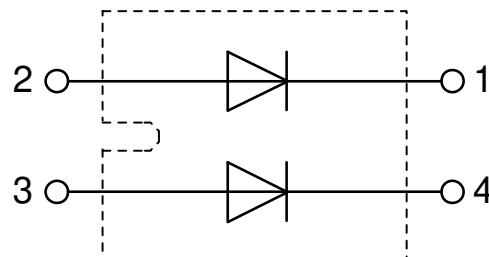
| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 2.92 | V |
| $R_{0\ max}$ | slope resistance * | 55 | mΩ |



Outlines SOT-227B (minibloc)



| Dim. | Millimeter | | Inches | |
|------|------------|-------|--------|-------|
| | min | max | min | max |
| A | 31.50 | 31.88 | 1.240 | 1.255 |
| B | 7.80 | 8.20 | 0.307 | 0.323 |
| C | 4.09 | 4.29 | 0.161 | 0.169 |
| D | 4.09 | 4.29 | 0.161 | 0.169 |
| E | 4.09 | 4.29 | 0.161 | 0.169 |
| F | 14.91 | 15.11 | 0.587 | 0.595 |
| G | 30.12 | 30.30 | 1.186 | 1.193 |
| H | 37.80 | 38.23 | 1.488 | 1.505 |
| J | 11.68 | 12.22 | 0.460 | 0.481 |
| K | 8.92 | 9.60 | 0.351 | 0.378 |
| L | 0.74 | 0.84 | 0.029 | 0.033 |
| M | 12.50 | 13.10 | 0.492 | 0.516 |
| N | 25.15 | 25.42 | 0.990 | 1.001 |
| O | 1.95 | 2.13 | 0.077 | 0.084 |
| P | 4.95 | 6.20 | 0.195 | 0.244 |
| Q | 26.54 | 26.90 | 1.045 | 1.059 |
| R | 3.94 | 4.42 | 0.155 | 0.167 |
| S | 4.55 | 4.85 | 0.179 | 0.191 |
| T | 24.59 | 25.25 | 0.968 | 0.994 |
| U | -0.05 | 0.10 | -0.002 | 0.004 |
| V | 3.20 | 5.50 | 0.126 | 0.217 |
| W | 19.81 | 21.08 | 0.780 | 0.830 |
| Z | 2.50 | 2.70 | 0.098 | 0.106 |



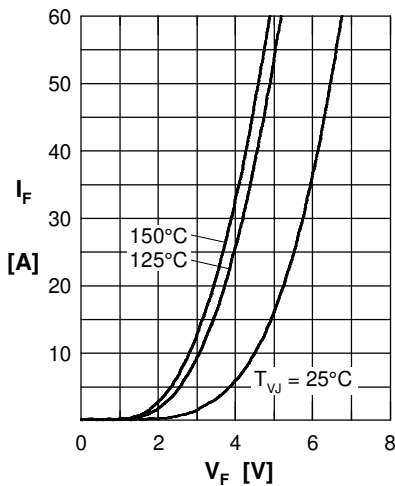
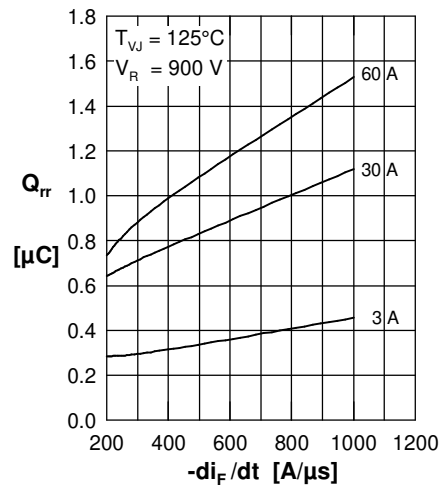
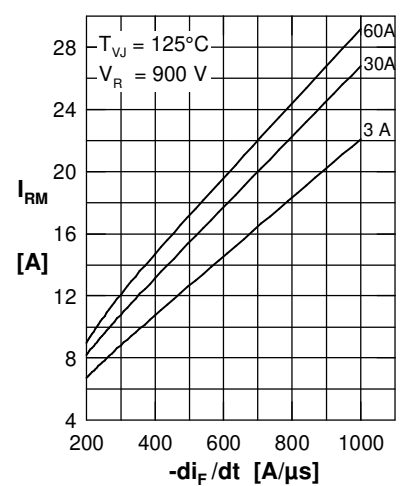
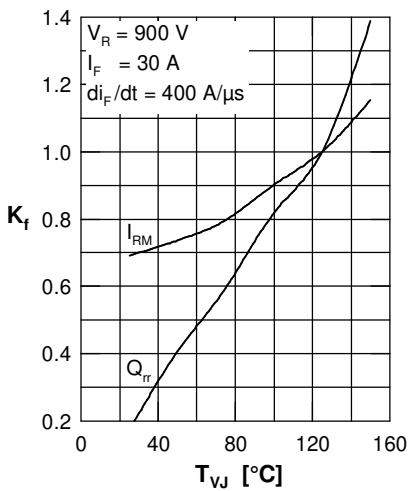
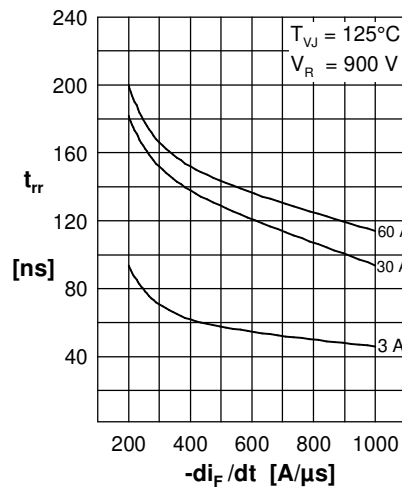
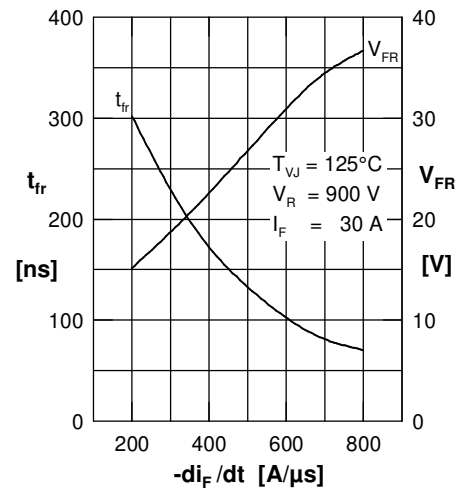
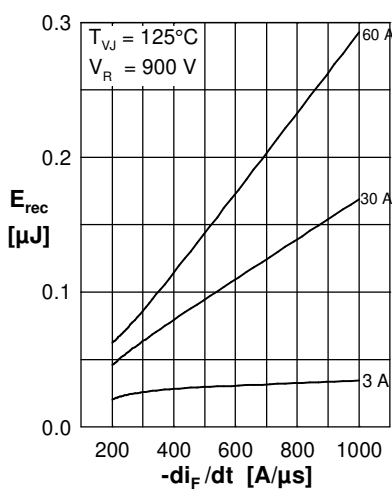
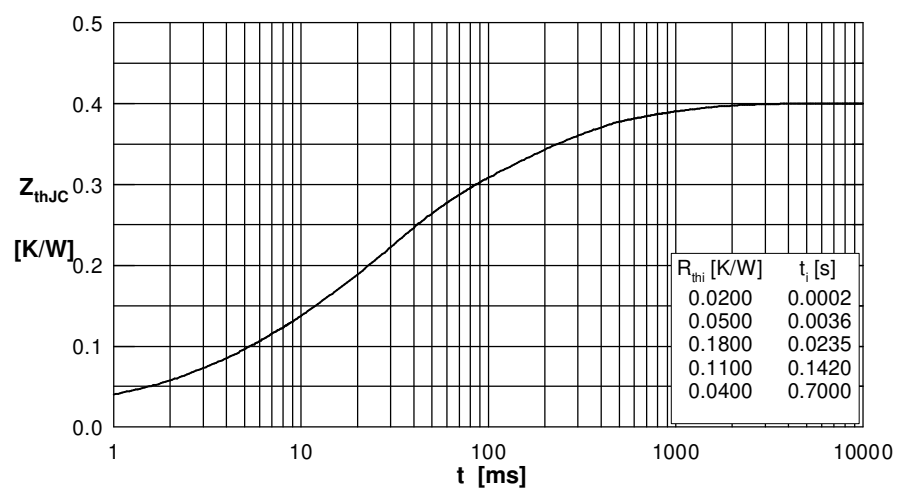
Fast Diode

 Fig. 1 Typ. Forward current I_F versus V_F

 Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

 Fig. 3 Typ. reverse recov. current I_{RM} versus $-di_F/dt$

 Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

 Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

 Fig. 6 Typ. forward recov. voltage V_{FR} & time t_{fr} versus di_F/dt

 Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$


Fig. 8 Transient thermal impedance junction to case